

IN THE CLAIMS:

Please revise the claims to read as follows.

1. (Currently amended) A group III nitride compound semiconductor light-emitting device, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; ~~and~~

an n-type clad layer being in contact with said light-emitting ~~layer, layer, and~~
an intermediate layer being in contact with said n-type clad layer at one face thereof
and an n-type contact layer at another face thereof.

wherein said n-type clad layer is made thicker than each of said barrier layers ~~and the~~
~~thickness of said n-type clad layer is in a range of 100 Å to 500 Å, and~~

~~wherein said n-type clad layer is formed of a material substantially the same as said~~
~~barrier layers, by having been formed under substantially same conditions~~

wherein said intermediate layer comprises $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0 < x < 1)$.

2-3. (Canceled)

4-5. (Cancel)

6. (Currently amended) A group III nitride compound semiconductor light-emitting device according to claim 4 1, wherein said intermediate layer comprises $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0.01 \leq x \leq 0.05)$.

7. (Currently amended) The group III nitride compound semiconductor light-emitting device of claim ~~1~~ 33, wherein said n-type clad layer and said barrier layers comprise GaN.

8. (Previously presented) The semiconductor light-emitting device of claim 1, wherein a thickness of said well layer is approximately 30 Å and a thickness of said barrier layer is approximately 70 Å.

9. (Previously presented) The semiconductor light-emitting device of claim 1, further comprising:

a cap layer formed on said light-emitting layer, said cap layer being formed of a material substantially the same as said barrier layers; and

a p-type clad layer formed on and contacting said cap layer.

10. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 180 Å to 500 Å, and a light emitted comprises green light in a wavelength range of approximately 510 nm to 530 nm.

11. (Previously presented) The semiconductor light-emitting device of claim 10, wherein said thickness of said p-type clad layer is in a range of approximately 240 Å to 360 Å.

12. (Previously presented) The semiconductor light-emitting device of claim 9, wherein a thickness of said p-type clad layer is in a range of approximately 90 Å to 390 Å, and a light emitted comprises blue light in a wavelength range of approximately 460 nm to 475 nm.

13. (Previously presented) The semiconductor light-emitting device of claim 12, wherein said thickness of said p-type clad layer is in a range of approximately 120 Å to 300 Å.

14. (Previously presented) The semiconductor light-emitting device of claim 9, wherein said p-type clad layer comprises p-type doped $\text{Al}_x\text{Ga}_{1-x}\text{N}$, where x ranges from approximately 0.10 to 0.14.

15-16. (Cancel)

17. (Currently amended) The group III nitride compound semiconductor light-emitting device of claim ~~15~~ 1, further comprising:

a cap layer in contact with said light-emitting layer on a side of said light-emitting layer opposite to that contacting said n-type clad layer, said cap layer being formed of a material substantially the same as said barrier layers.

18. (Currently amended) A group III nitride compound semiconductor light-emitting device (LED) having enhanced color purity, comprising:

a light-emitting layer of a multilayer quantum well structure comprising alternately laminated well layers and barrier layers; ~~and~~

an n-type clad layer being in contact with said light-emitting layer on a first surface;

a cap layer being in contact with said light-emitting layer on a second surface opposite said first surface; and

an intermediate layer being in contact with said n-type clad layer at one face thereof and an n-type contact layer at another face thereof,

wherein said n-type clad layer, said cap layer and each of said barrier layers are formed of a ~~material substantially the same, by being formed under substantially the same conditions,~~

~~said substantially same material thereby~~ material, thereby providing ~~a substantially same strain~~
~~on said multilayer quantum well structure that provides~~ an enhanced color purity of light
emitted from said light emitting layer and

wherein said intermediate layer comprises $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0 < x < 1)$.

19. (Previously presented) The LED of claim 18, wherein said substantially same material comprises GaN.

20. (Currently amended) The LED of claim ~~17~~ 18, further comprising:

a ~~p-clad~~ p-type clad layer on said cap layer, said p-clad layer having a thickness selected from a range of thickness that optimizes an intensity of said color.

21. (Currently amended) The LED of claim 20, wherein said color comprises a green light in a main wavelength range of approximately 510 nm to 530 nm and said range of thickness of said ~~p-clad~~ p-type clad layer is approximately 180 Å to 500 Å.

22. (Previously presented) The LED of claim 21, wherein said range of thickness is approximately 240 Å to 360 Å.

23. (Currently amended) The LED of claim 20, wherein said color comprises a blue light in a main wavelength range of approximately 460 nm to 475 nm and said range of thickness of said ~~p-clad~~ p-type clad layer is approximately 90 Å to 390 Å.

24. (Previously presented) The LED of claim 23, wherein said range of thickness is approximately 120 Å to 300 Å.

25. (Previously presented) The LED of claim 20, wherein said p-type clad layer comprises a p-type doped $\text{Al}_x\text{Ga}_{1-x}\text{N}$, wherein $0.10 \leq x \leq 0.14$.

26. (Previously presented) The LED of claim 18, said n-type clad layer is made thicker than each of said barrier layers and a thickness of said n-type clad layer is in a range of 100 Å to 500 Å.

27-28. (Cancel)

29. (Currently amended) The LED of claim ~~27~~ 18, wherein $0.01 \leq x \leq 0.05$.

30-31. (Cancel)

32. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein a thickness of said n-type clad layer is in a range of 100 Å to 500 Å.

33. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said n-type clad layer is formed of a material substantially the same as said barrier layers.

34. (New) A group III nitride compound semiconductor light-emitting device according to claim 17, wherein said n-type clad layer, said cap layer, and said barrier layers comprise GaN.
35. (New) A group III nitride compound semiconductor light-emitting device according to claim 1, wherein said intermediate layer consists of $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0 < x < 1)$.
36. (New) A group III nitride compound semiconductor light-emitting device according to claim 18, wherein said intermediate layer consists of $\text{In}_x\text{Ga}_{1-x}\text{N}$, where $(0 < x < 1)$.